

REMARKS

The Official Action dated October 18, 2002 has been received and its contents carefully noted. In view thereof, Applicant hereby elects what the Examiner has indicated as Group I, drawn to a semiconductor device, classified in class 257, subclass 774 including at least claims 1-7 for examination on the merits. Early allowance of the elected claims is earnestly solicited.

Further with respect to Applicant's response to the Restriction Requirement, as can be seen from the foregoing amendments, claims 1 and 8 have been amended in order to better define that which Applicants' regard as the invention. Again, examination on the merits and early allowance of the subject application is earnestly solicited.

Should the Examiner believe a conference would be of benefit in expediting the prosecution of the subject application, he is hereby invited to telephone council to arrange such a conference.

Respectfully submitted,



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Version Showing Changes Made:

1. (Amended) A semiconductor device comprising:

metal interconnects made from a multi-layer film composed of a first metal film deposited on a semiconductor substrate with an insulating film sandwiched therebetween and a second metal film deposited on said first metal film, wherein the second metal film is a seed layer

an interlayer insulating film formed on said metal interconnects; and

a plug made from a third metal film selectively grown on said second metal film within a via hole formed in said interlayer insulating film.

8. (Amended) A method for fabricating a semiconductor device comprising the steps of:

depositing a first metal film on a semiconductor substrate with an insulating film sandwiched therebetween;

depositing a second metal film on said first metal film, wherein the second metal film is a seed layer;

forming an interlayer insulating film on said second metal film;

forming a via hole in said interlayer insulating film so as to expose said second metal film within said via hole;

forming a plug of a third metal film selectively grown on said second metal film within said via hole;

forming a patterned interlayer insulating film by patterning said interlayer insulating film into the shape of interconnects; and

forming metal interconnects from a multi-layer film composed of said first metal film and said second metal film by etching said multi-layer film with said plug and said patterned interlayer insulating film used as a mask.